NPN SILICON RF POWER TRANSISTOR

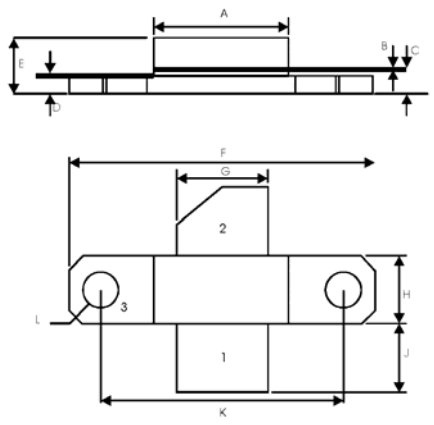
DESCRIPTION:

The **MRA0610-40A** is Designed for Class C, Common Base Wideband Large Signal Amplifier Applications From 600 MHz to 1.0 GHz, With Internal Compensating Matching Network and Diffused Ballast Resistors.

MAXIMUM RATINGS

I_C	5.0 A (CONT)
V_{CES}	50 V
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	2.5 °C/W

PACKAGE STYLE MRA .25



DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	8.00	8.38	O.351	0.330
B	0.08	0.15	0.003	0.006
C	1.98	2.34	0.078	0.092
D	1.40	1.65	0.055	0.065
E	4.32	5.08	0.170	0.200
F	18.77	19.03	0.739	0.749
G	5.33	5.84	0.210	0.230
H	6.17	6.43	0.243	0.253
J	7.74	8.64	0.210	0.240
K	14.10	14.35	0.555	0.565
L	3.17	3.43	0.125	0.135

2 = Collector 1 = Emitter
3 = Base

CHARACTERISTICS $T_C = 25\ ^oC$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	I_C = 100 mA	50			V
BV_{EBO}	I_E = 1.25 mA	3.5			V
I_{CBO}	V_{CB} = 28 V			5.0	mA
h_{FE}	V_{CE} = 5.0 V I_C = 500 mA	10		100	---
C_{ob}	V_{CB} = 28 V f = 1.0 MHz			28	pF
G_{PB}	V_{CE} = 28 V P_{out} = 18 W f = 600 MHz & 1.0 GHz	7.0			dB
η_C		50			%